# MOSFET - Single, P-Channel, Small Signal, SOT-883 (XDFN3), 1.0 x 0.6 x 0.4 mm

-20 V, -281 mA

#### **Features**

- Single P-Channel MOSFET
- Ultra Low Profile SOT–883 (XDFN3) 1.0 x 0.6 x 0.4 mm for Extremely Thin Environments Such as Portable Electronics
- Low R<sub>DS(on)</sub> Solution in the Ultra Small 1.0 x 0.6 mm Package
- 1.5 V Gate Drive
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

### **Applications**

- High Side Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Solutions

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V <sub>DSS</sub>	-20	V
Gate-to-Source Voltage			V <sub>GS</sub>	±8	V
Continuous Drain	Steady State	, ,		-281	mA
Current (Note 1)	State	T <sub>A</sub> = 85°C		-202	
	t ≤ 5 s	T <sub>A</sub> = 25°C		-332	
Power Dissipation (Note 1)	Steady State	T <sub>A</sub> = 25°C	$P_{D}$	155	mW
	t ≤ 5 s			218	
Pulsed Drain Current	t <sub>p</sub> = 10 μs		I <sub>DM</sub>	-842	mA
Operating Junction and Storage Temperature			T <sub>J</sub> , T <sub>STG</sub>	–55 to 150	°C
Source Current (Body Diode) (Note 2)			Is	-130	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- Surface-mounted on FR4 board using the minimum recommended pad size, or 2 mm<sup>2</sup>, 1 oz Cu.
- 2. Pulse Test: pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2%

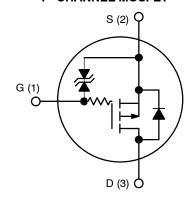


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V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> MAX	I <sub>D</sub> Max
	1.3 Ω @ -4.5 V	
-20 V	2.0 Ω @ -2.5 V	–281 mA
-20 V	3.4 Ω @ -1.8 V	-201 IIIA
	4.5 Ω @ -1.5 V	

#### **P-CHANNEL MOSFET**



#### MARKING DIAGRAM



SOT-883 (XDFN3) CASE 506CB



65 = Specific Device Code M = Date Code

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NTNS3A65PZT5G	SOT-883 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit	
Junction-to-Ambient - Steady State (Note 3)		804	°C ///	
Junction-to-Ambient - t ≤ 5 s (Note 3)	$R_{\theta JA}$	574	°C/W	

<sup>3.</sup> Surface–mounted on FR4 board using the minimum recommended pad size, or 2 mm<sup>2</sup>, 1 oz Cu.

## **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise stated)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS	•						
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /	I <sub>D</sub> = -250 μA, ref to 25°C			11		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 \text{ V},$ $V_{DS} = -20 \text{ V}$	T <sub>J</sub> = 25°C			-1	μΑ
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±	5 V			±10	μΑ
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_D = -250 \mu A$		-0.4		-1.0	V
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>				2.2		mV/°C
Drain-to-Source On Resistance		$V_{GS} = -4.5 \text{ V}, I_D = -200 \text{ mA}$			0.9	1.3	Ω
		$V_{GS} = -2.5 \text{ V}, I_D = -100 \text{ mA}$			1.3	2.0	
	R <sub>DS(on)</sub>	$V_{GS} = -1.8 \text{ V}, I_D = -50 \text{ mA}$			1.8	3.4	
		$V_{GS}$ = -1.5 V, $I_D$ = -10 mA			2.3	4.5	Ω
Forward Transconductance	9FS	$V_{DS} = -5 \text{ V}, I_D = -200 \text{ mA}$			0.58		S
Source-Drain Diode Voltage	$V_{SD}$	$V_{GS} = 0 \text{ V}, I_{S} = -100 \text{ mA}$			-0.8	-1.2	V
CHARGES & CAPACITANCES							
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, freq = 1 MHz, V <sub>DS</sub> = -10 V			44		
Output Capacitance	C <sub>OSS</sub>				6.7		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>				5.5		]
Total Gate Charge	Q <sub>G(TOT)</sub>	$V_{GS} = -4.5 \text{ V}, V_{DS} = -10 \text{ V};$ $I_{D} = -200 \text{ mA}$			1.1		
Threshold Gate Charge	Q <sub>G(TH)</sub>				0.1		nC
Gate-to-Source Charge	$Q_{GS}$				0.2		
Gate-to-Drain Charge	$Q_{GD}$				0.2		
SWITCHING CHARACTERISTICS, V <sub>GS</sub>	= <b>4.5 V</b> (Note 4	1)					
Turn-On Delay Time	t <sub>d(ON)</sub>				18		
Rise Time	t <sub>r</sub>	$V_{GS}$ = -4.5 V, $V_{DD}$ = -10 V, $I_D$ = -200 mA, $R_G$ = 2 $\Omega$			32		]
Turn-Off Delay Time	t <sub>d(OFF)</sub>				178		ns
Fall Time	t <sub>f</sub>				84		

<sup>4.</sup> Switching characteristics are independent of operating junction temperatures

#### **TYPICAL CHARACTERISTICS**

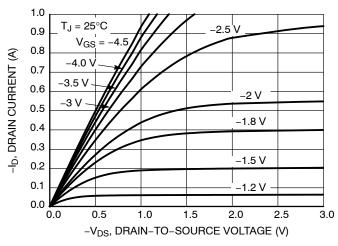


Figure 1. On-Region Characteristics

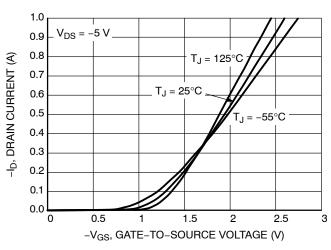


Figure 2. Transfer Characteristics

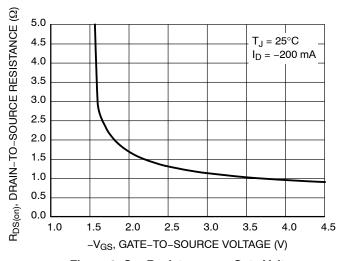


Figure 3. On-Resistance vs. Gate Voltage

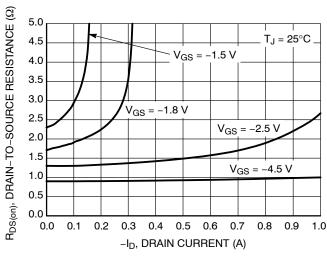


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

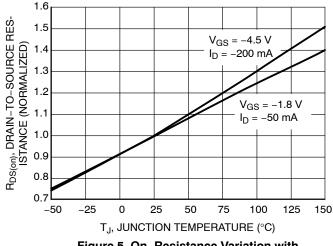


Figure 5. On–Resistance Variation with Temperature

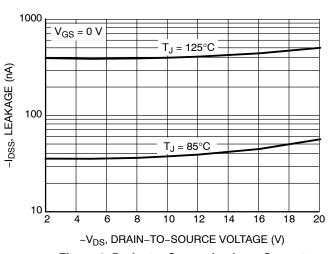


Figure 6. Drain-to-Source Leakage Current vs. Voltage

#### **TYPICAL CHARACTERISTICS**

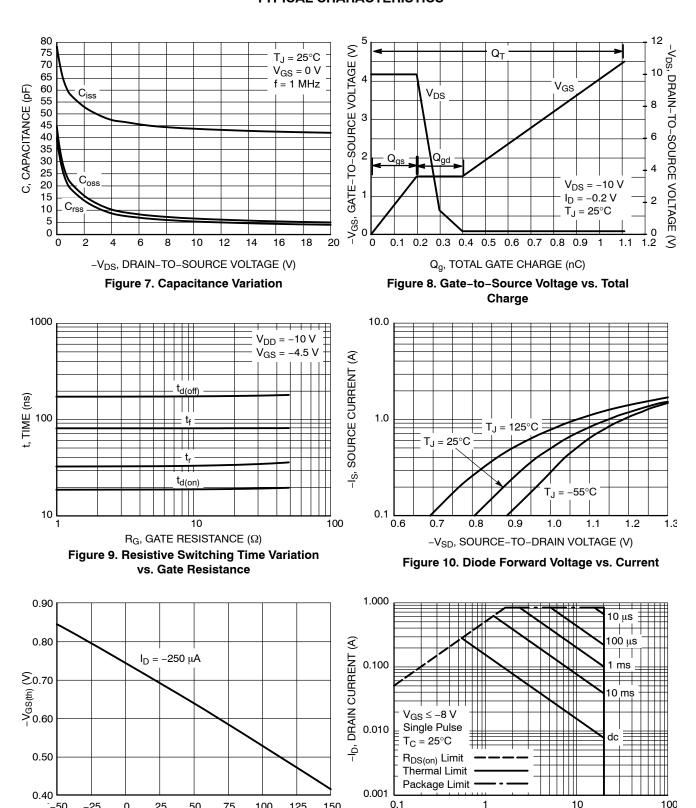


Figure 12. Maximum Rated Forward Biased **Safe Operating Area** 

-V<sub>DS</sub>, DRAIN-TO-SOURCE VOLTAGE (V)

-50

-25

0

25

50

T.J, STARTING JUNCTION TEMPERATURE (°C)

Figure 11. Threshold Voltage

75

100

125

150

## **TYPICAL CHARACTERISTICS**

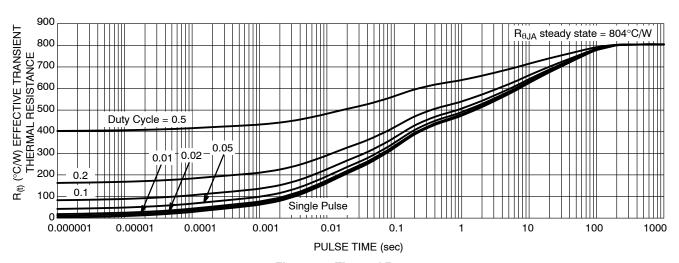


Figure 13. Thermal Response

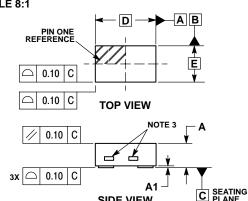


## SOT-883 (XDFN3), 1.0x0.6, 0.35P

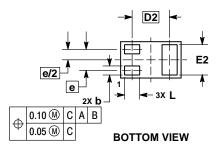
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**DATE 30 MAR 2012** 

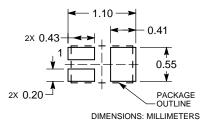




SIDE VIEW



#### **RECOMMENDED SOLDER FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. EXPOSED COPPER ALLOWED AS SHOWN.

	MILLIMETERS				
DIM	MIN	MAX			
Α	0.340	0.440			
A1	0.000	0.030			
b	0.075	0.200			
D	0.950	1.075			
D2	0.620 BSC				
е	0.350 BSC				
Е	0.550	0.675			
E2	0.425	0.550			
L	0.170	0.300			

#### **GENERIC** MARKING DIAGRAM\*



XX = Specific Device Code

M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

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